

Title (en)

METHOD FOR GROWING SINGLE CRYSTAL OF SEMICONDUCTOR

Title (de)

VERFAHREN ZUR HERSTELLUNG VON EINKRISTALLEN FÜR HALBLEITER

Title (fr)

PROCEDE PERMETTANT DE FAIRE POUSSER DES MONOCRISTAUX DE SEMI-CONDUCTEUR

Publication

**EP 1199387 A1 20020424 (EN)**

Application

**EP 01904510 A 20010216**

Priority

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Abstract (en)

By utilizing a crystal pulling apparatus for producing a single crystal according to the Czochralski method comprising at least a crucible to be charged with a raw material, a heater surrounding the crucible, and subsidiary heating means provided below the crucible, a single crystal is pulled or the raw material is additionally introduced with heating by the heater surrounding the crucible and the subsidiary heating means when the amount of the raw material melt in the crucible becomes a limited amount. Thus, there is provided a method for growing a single crystal at a high yield while preventing solidification of melt raw material decreased to a limited amount without affecting crystal quality, durability of crucible or the like even when a crucible having a large diameter is used. <IMAGE>

IPC 1-7

**C30B 15/14**; **C30B 29/06**

IPC 8 full level

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CPC (source: EP KR US)

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